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Shin et al.(10) **Pub. No.: US 2016/0141559 A1**(43) **Pub. Date: May 19, 2016**(54) **ORGANIC LIGHT EMITTING DIODE
DISPLAY DEVICE AND METHOD OF
FABRICATING THE SAME**(71) Applicant: **LG Display Co., Ltd.**, Seoul (KR)(72) Inventors: **Young-Hoon Shin**, Paju-si (KR);
Myung-Seop Kim, Goyang-si (KR);
Jun-Ho Lee, Seoul (KR)(21) Appl. No.: **15/003,716**(22) Filed: **Jan. 21, 2016****Related U.S. Application Data**(62) Division of application No. 14/087,379, filed on Nov.
22, 2013, now Pat. No. 9,281,499.(30) **Foreign Application Priority Data**

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(57)

ABSTRACT

An organic light emitting diode display device comprises: first and second substrates facing and spaced apart from each other; a gate line and a data line on the first substrate, the gate line and the data line crossing each other to define a plurality of pixel regions; at least one thin film transistor coupled to the gate line and the data line; a light emitting diode coupled to the at least one thin film transistor, the light emitting diode including a first electrode, an emitting layer and a second electrode; and a passivation layer on the light emitting diode, the passivation layer having a smaller area than the second electrode.

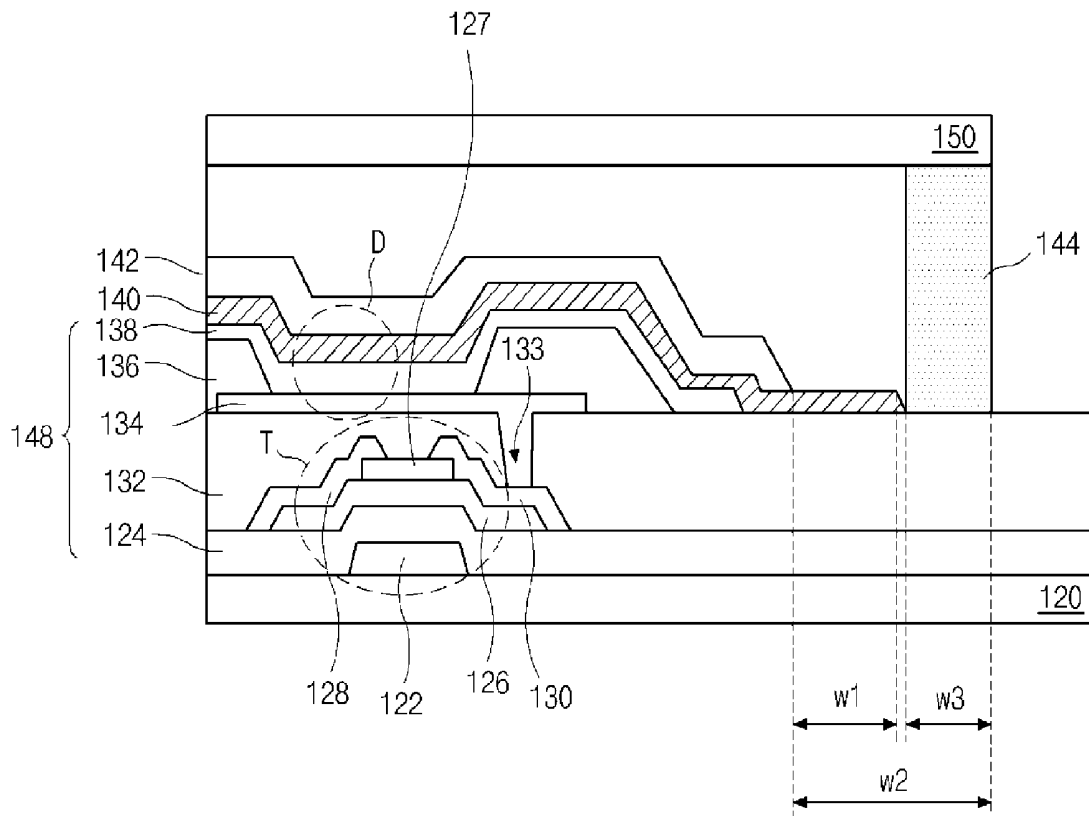


FIG. 1
(Related Art)

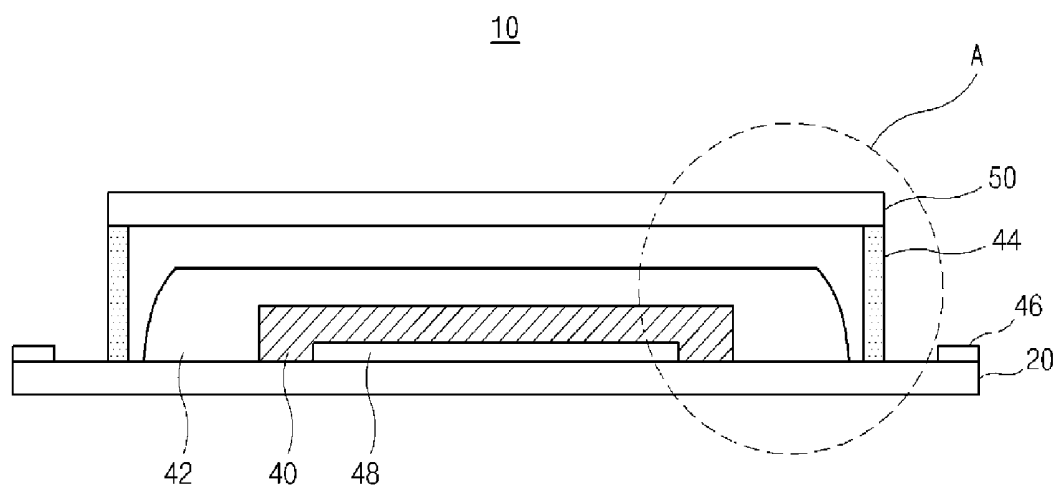


FIG. 2
(Related Art)

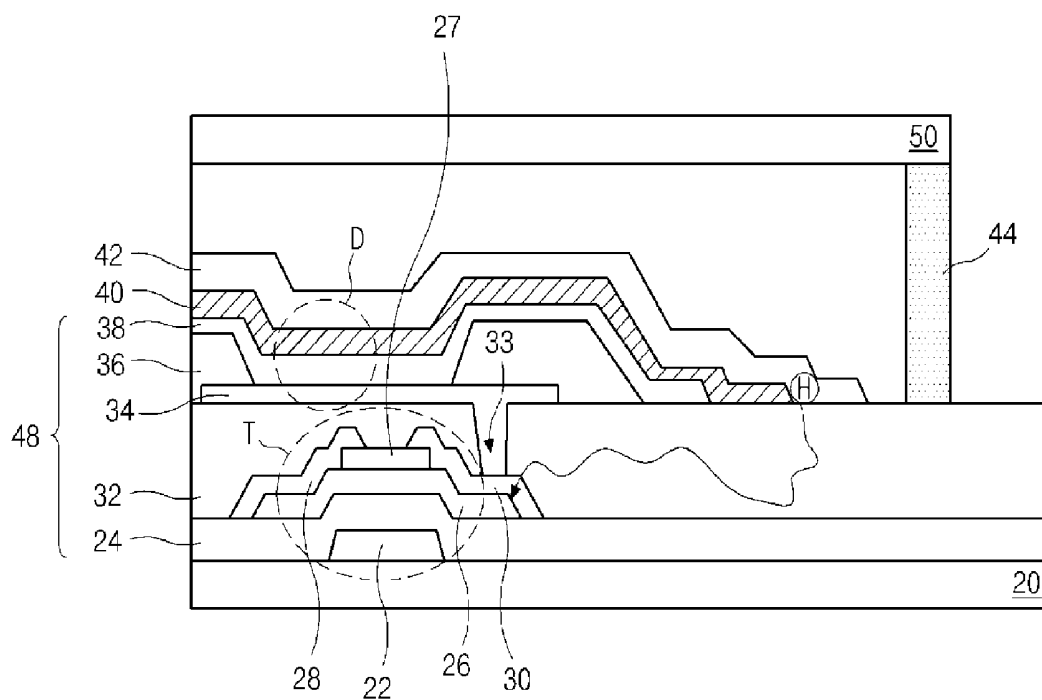


FIG. 3

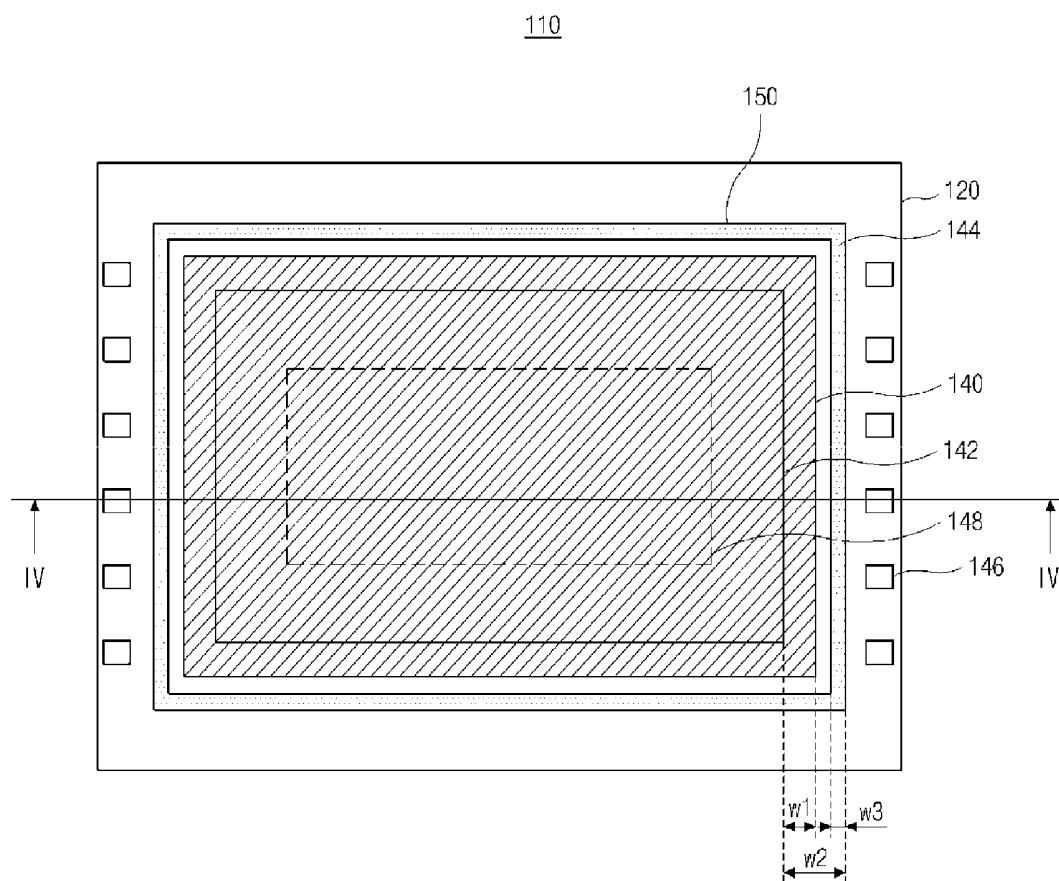


FIG. 4

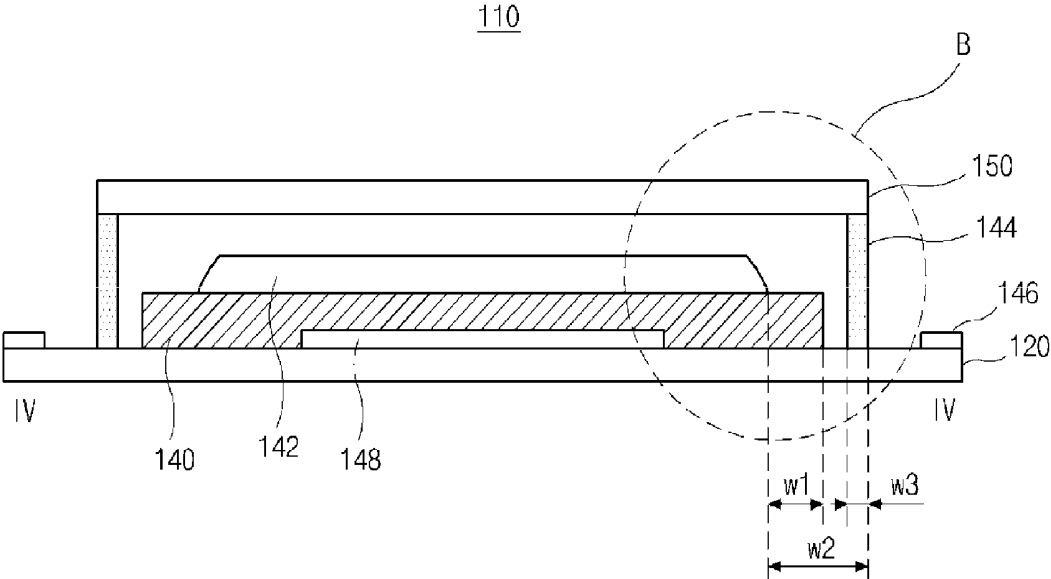


FIG. 6

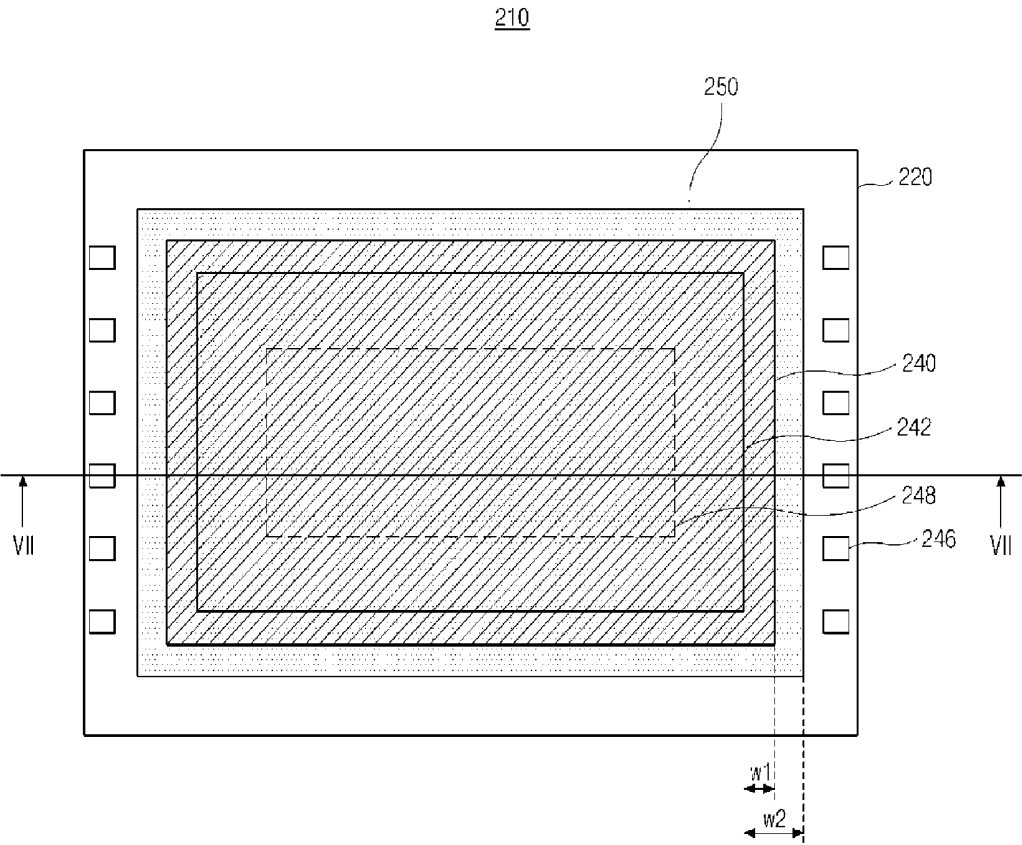
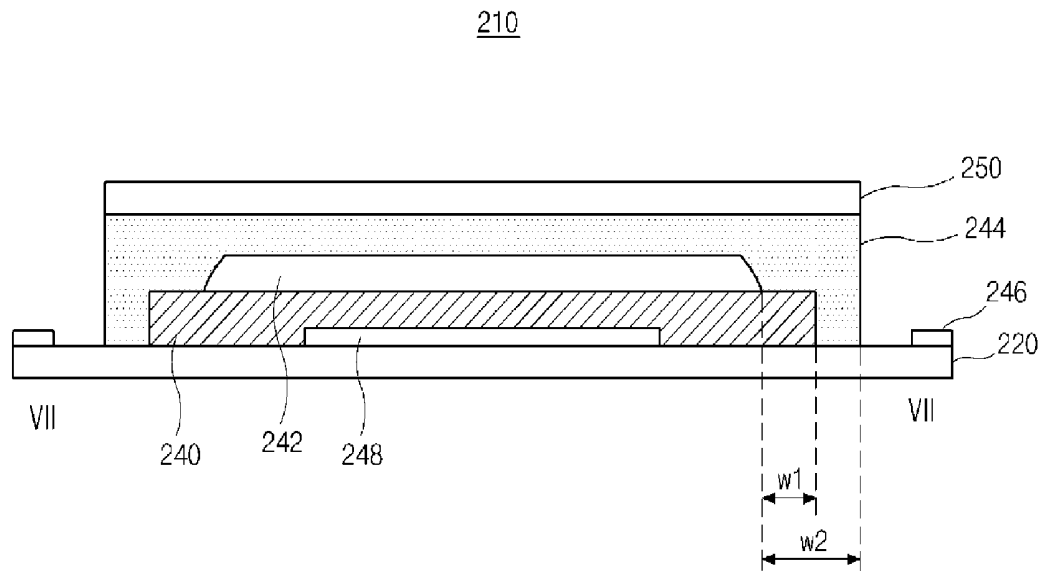


FIG. 7



ORGANIC LIGHT EMITTING DIODE DISPLAY DEVICE AND METHOD OF FABRICATING THE SAME

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application is a divisional application under 35 U.S.C. §121 of U.S. patent application Ser. No. 14/087,379, filed on Nov. 22, 2013, which claims priority from and the benefit under 35 U.S.C. §119(a) to Korean Patent Application No. 10-2012-0146781, filed on Dec. 14, 2012, both of which are hereby incorporated by reference for all purposes as if fully set forth herein.

BACKGROUND

[0002] 1. Technical Field

[0003] The present disclosure relates to an organic light emitting diode (OLED) display device, and more particularly, to an OLED display device where a passivation layer has a smaller area than an upper electrode of a light emitting diode and a method of fabricating the OLED display device.

[0004] 2. Discussion of the Related Art

[0005] Among various flat panel displays (FPDs), an organic light emitting diode (OLED) display device has superior properties such as high brightness and an ability to be driven by a low voltage. Since the OLED display device is an emissive type, the OLED display device has high contrast ratio and thin profile. The OLED display device has an advantage in displaying a moving image due to the low response time of several micro seconds (μsec). The OLED display device has no limitation on a viewing angle and is stable even in a low temperature. Since the OLED display device is driven by a low voltage of 5V to 15V in direct current (DC), it is easy to fabricate and design a driving circuit.

[0006] In addition, since a fabrication process of the OLED display device requires only a deposition apparatus and an encapsulating apparatus, the fabrication process of the OLED display device is simple.

[0007] The OLED display device includes a plurality of pixel regions, and a switching thin film transistor (TFT) and a driving TFT are formed in each of the plurality of pixel regions. Generally, the TFTs are formed by using a semiconductor material such as amorphous silicon.

[0008] Recently, to meet the requirements of large size and high resolution, the OLED display device including the TFTs having faster signal process, more stable operation and durability is required. However, the TFT using amorphous silicon has a relatively low mobility (e.g., less than $1 \text{ cm}^2/\text{Vsec}$), which presents challenges in developing the OLED display device with large size and high resolution.

[0009] Accordingly, an oxide TFT including an active layer of an oxide semiconductor material, which has excellent electrical properties such as high mobility and low leakage current can be used to obviate some of these shortcomings.

[0010] Figure (FIG. 1) is a cross-sectional view showing an organic light emitting diode display device according to the related art, and FIG. 2 is a magnified view of a portion A of FIG. 1.

[0011] In FIGS. 1 and 2, an organic light emitting diode (OLED) display device 10 includes first and second substrates 20 and 50, an array layer 48, a second electrode 40 and

a passivation layer 42 sequentially on the first substrate 20 and a seal pattern 44 at an edge portion between the first and second substrates 20 and 50.

[0012] The first and second substrates 20 and 50 facing and spaced apart from each other include a plurality of pixel regions (not shown). The array layer 48 includes a gate line (not shown), a data line (not shown), a power line (not shown), a switching thin film transistor (TFT), a driving TFT T, a first electrode 34 and an emitting layer 38. Also, the gate line, the data line and the power line cross each other to form the plurality of pixel regions. In addition, the switching TFT is coupled to the gate line and the data line. Moreover, the driving TFT T is coupled to the switching TFT, the power line, and the first electrode 34 is connected to the driving TFT T. Furthermore, the first electrode 34, the emitting layer 38 and the second electrode 40 constitute a light emitting diode (LED) D.

[0013] The array layer 48 is disposed in a display region at a central portion of the first and second substrates 20 and 50. A gate electrode 22 is formed in each pixel region on an inner surface of the first substrate 20, and a gate insulating layer 24 is formed on the gate electrode 22. Also, an oxide semiconductor layer 26 is formed on the gate insulating layer 24 corresponding to the gate electrode 22, and an etch stopper 27 is formed on the oxide semiconductor layer 26. In addition, source and drain electrodes 28 and 30 are formed on both end portions, respectively, of the etch stopper 27 and the oxide semiconductor layer 26. The gate electrode 22, the oxide semiconductor layer 26, the source electrode 28 and the drain electrode 30 constitute the driving TFT T.

[0014] A protecting layer 32 is formed on the driving TFT T. The protecting layer 32 includes a drain contact hole 33 exposing the drain electrode 30 of the driving TFT T.

[0015] The first electrode 34 coupled to the driving TFT T is formed on the protecting layer 32 in each of the plurality of pixel regions, and a bank layer 36 is formed on a boundary portion of the first electrode 34. The bank layer 36 includes an opening exposing a central portion of the first electrode 34. The emitting layer 38 contacting the first electrode 34 through the opening is formed on the bank layer 36, and the second electrode 40 is formed on the emitting layer 38. The first electrode 34, the emitting layer 38 and the second electrode 40 constitute the LED D. In addition, the passivation layer 42 is formed on the second electrode 40.

[0016] The seal pattern 44 attaches the first and second substrates 20 and 50, and a plurality of pads 46 coupled to a driving circuit (not shown) are formed on the first substrate 20 outside the seal pattern 44. The first substrate 20 is referred to as a lower substrate, a TFT substrate or a backplane, and the second substrate 50 is referred to as an encapsulation substrate.

[0017] In the OLED display device 10, each of the second electrode 40 where a common voltage is applied and the passivation layer 42 protecting the LED D from an exterior moisture or an exterior contaminant are formed as a single body covering the plurality of pixel regions. As a result, each of the second electrode 40 and the passivation layer 42 is formed on an entire surface of the first substrate 20.

[0018] The passivation layer 42 is formed by a plasma chemical vapor deposition (PCVD) apparatus or a physical vapor deposition (PVD) apparatus such as a sputter. In one exemplary embodiment, silicon nitride (SiN_x) film, silicon oxynitride (SiON) film or silicon oxide (SiO_x) film formed by

the PCVD apparatus or alumina (AlOx) film formed by the sputter may be used as the passivation layer 42.

[0019] However, when the passivation layer 42 is formed of silicon compound by the PCVD apparatus, a deposition process should be performed under a relatively low temperature (e.g., less than about 100° C.) to prevent deterioration of the emitting layer 38. Due to the relatively low temperature, source gases do not completely react and hydrogen (H) from the source gases such as silane (SiH₄) gas or ammonia (NH₃) gas remains in the passivation layer 42.

[0020] The hydrogen is diffused into the oxide semiconductor layer 26 of the driving TFT T through the protecting layer 32 to generate a reduction process of the oxide semiconductor material of the oxide semiconductor layer 26. The reduction of the oxide semiconductor material due to the hydrogen results in a threshold voltage shift of the driving TFT T, and the threshold voltage shift causes deterioration such as a stain or brightness deviation in an image. As a result, a displaying quality of the OLED display device 10 is degraded.

SUMMARY

[0021] Embodiments of the present invention relate to an organic light emitting diode display device and a method of fabricating the organic light emitting diode display device. Accordingly, one exemplary embodiment is directed to an organic light emitting diode display device that substantially obviates one or more of the problems due to limitations and disadvantages of the related art.

[0022] One exemplary embodiment is an organic light emitting diode display device, where reduction of an oxide semiconductor material is prevented by an upper electrode having a larger area than a passivation layer, and a method of fabricating the organic light emitting diode display device.

[0023] In addition, one exemplary embodiment is an organic light emitting diode display device, where deterioration is prevented and display quality is improved by an upper electrode having a larger area than a passivation layer, and a method of fabricating the organic light emitting diode display device.

[0024] Advantages and features of the disclosure will be set forth in part in the description, which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the invention. Other advantages and features of the embodiments herein may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0025] To achieve other advantages and features in accordance with the purpose according to one aspect of the invention, one exemplary embodiment is an organic light emitting diode display device comprising: first and second substrates facing and spaced apart from each other; a gate line and a data line on the first substrate, the gate line and the data line crossing each other to define a plurality of pixel regions; at least one thin film transistor coupled to the gate line and the data line; a light emitting diode coupled to the at least one thin film transistor, the light emitting diode including a first electrode, an emitting layer and a second electrode; and a passivation layer on the light emitting diode, and the passivation layer having a smaller area than the second electrode.

[0026] In another aspect, one exemplary embodiment is a method of fabricating an organic light emitting diode display device, comprising: forming a gate line and a data line on a

first substrate, the gate line and the data line crossing each other to define a plurality of pixel regions; forming at least one thin film transistor coupled to the gate line and the data line; forming a light emitting diode coupled to the at least one thin film transistor, the light emitting diode including a first electrode, an emitting layer and a second electrode; forming a passivation layer on the light emitting diode, the passivation layer having a smaller area than the second electrode; and attaching a second substrate to the first substrate having the passivation layer.

[0027] It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory, and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0028] The accompanying drawings, which are included to provide a further understanding of the invention, are incorporated in and constitute a part of this specification, illustrate implementations of the invention and together with the description serve to explain the principles of the invention.

[0029] FIG. 1 is a cross-sectional view showing an organic light emitting diode display device according to the related art.

[0030] FIG. 2 is a magnified view of a portion A of FIG. 1.

[0031] FIG. 3 is a plan view showing an organic light emitting diode display device according to a first embodiment of the present invention.

[0032] FIG. 4 is a cross-sectional view taken along a line IV-IV of FIG. 3.

[0033] FIG. 5 is a magnified view of a portion B of FIG. 4.

[0034] FIG. 6 is a plan view showing an organic light emitting diode display device according to a second embodiment of the present invention.

[0035] FIG. 7 is a cross-sectional view taken along a line VII-VII of FIG. 6.

DETAILED DESCRIPTION

[0036] Reference will now be made in detail to embodiments of the present invention, examples of which are illustrated in the accompanying drawings. In the following description, when a detailed description of well-known functions or configurations related to this document is determined to unnecessarily cloud a gist of the invention, the detailed description thereof will be omitted. The progression of processing steps and/or operations described is an example; however, the sequence of steps and/or operations is not limited to that set forth herein and may be changed as is known in the art, with the exception of steps and/or operations necessarily occurring in a certain order. Like reference numerals designate like elements throughout. Names of the respective elements used in the following explanations are selected only for convenience of writing the specification and may be thus different from those used in actual products.

[0037] FIG. 3 is a plan view showing an organic light emitting diode display device according to a first embodiment of the present invention, FIG. 4 is a cross-sectional view taken along a line IV-IV of FIG. 3, and FIG. 5 is a magnified view of a portion B of FIG. 4.

[0038] In FIG. 3, FIG. 4 and FIG. 5, an organic light emitting diode (OLED) display device 110 includes first and second substrates 120 and 150, an array layer 148, a second electrode 140 and a passivation layer 142 sequentially on the

first substrate **120** and a seal pattern **144** in an edge portion between the first and second substrates **120** and **150**.

[0039] The first and second substrates **120** and **150** facing and spaced apart from each other include a plurality of pixel regions (not shown). The array layer **148** includes a gate line (not shown), a data line (not shown), a power line (not shown), a switching thin film transistor (TFT), a driving TFT T, a first electrode **134** and an emitting layer **138**. In addition, the gate line, the data line and the power line cross each other to form the plurality of pixel regions. Also, the switching TFT is coupled to the gate line and the data line, and the driving TFT T is coupled to the switching TFT and the power line. The first electrode **134** is connected to the driving TFT T. Furthermore, the first electrode **134**, the emitting layer **138** and the second electrode **140** constitute a light emitting diode (LED) D.

[0040] The array layer **148** is disposed in a display region at a central portion of the first and second substrates **120** and **150**, and emits light for displaying an image. A gate electrode **122** is formed in each pixel region on an inner surface of the first substrate **120** and a gate insulating layer **124** is formed on the gate electrode **122**. An oxide semiconductor layer **126** is formed on the gate insulating layer **124** corresponding to the gate electrode **122**, and an etch stopper **127** is formed on the oxide semiconductor layer **126**.

[0041] Source and drain electrodes **128** and **130** are formed on the etch stopper **127**. The source and drain electrodes **128** and **130** contact both end portions, respectively, of the oxide semiconductor layer **126**. The gate electrode **122**, the oxide semiconductor layer **126**, the source electrode **128** and the drain electrode **130** constitute the driving TFT T.

[0042] The oxide semiconductor layer **126** may include an oxide semiconductor material such as indium gallium zinc oxide (IGZO), zinc indium oxide (ZIO), zinc gallium oxide (ZGO) and zinc tin oxide (ZTO). As a result, the driving TFT T may have excellent electrical properties such as a relatively high mobility, a relatively low leakage current and a relatively constant static current.

[0043] A protecting layer **132** is formed on the driving TFT T. The protecting layer **132** includes a drain contact hole **133** exposing the drain electrode **130** of the driving TFT T.

[0044] The first electrode **134** is formed on the protecting layer **132** in each of the plurality of pixel regions, and a bank layer **136** is formed on a boundary portion of the first electrode **134**. The first electrode **134** is electrically coupled to the drain electrode **130** of the driving TFT T through the drain contact hole **133**. The bank layer **136** includes an opening, exposing a central portion of the first electrode **134**.

[0045] The emitting layer **138** contacting the first electrode **134** through the opening is formed on the bank layer **136**, and the second electrode **140** is formed on the emitting layer **138**. The first electrode **134**, the emitting layer **138** and the second electrode **140** constitute the LED D. In addition, the passivation layer **142** is formed on the second electrode **140**.

[0046] The seal pattern **144** attaches the first and second substrates **120** and **150**, and a plurality of pads **146** coupled to a driving circuit (not shown) are formed on the first substrate **120** outside the seal pattern **144**. The first substrate **120** is referred to as a lower substrate, a TFT substrate or a back-plane, and the second substrate **150** is referred to as an encapsulation substrate.

[0047] In the OLED display device **110**, each of the second electrode **140** where a common voltage is applied, and the passivation layer **142** protecting the LED D from exterior

moisture or an exterior contaminant, are formed as a single body covering the plurality of pixel regions. As a result, each of the second electrode **140** and the passivation layer **142** is formed on an entire surface of the first substrate **120**. In addition, the second electrode **140** is formed to have a larger area than the passivation layer **142**, such that the passivation layer **142** is formed only on the second electrode **140**. Accordingly, the passivation layer **142** is formed inside a boundary of the second electrode **140**.

[0048] For example, when each of the second electrode **140** and the passivation layer **142** is formed to have a rectangular shape, four sides of the second electrode **140** may be exposed outside the passivation layer **142** and the seal pattern **144** may be formed in a region between the boundary of the second electrode **140** and the boundary of the second substrate **150**.

[0049] When the second electrode **140** is formed to exceed the seal pattern **144** and have a larger area than the second substrate **150**, the second electrode **140** may be corroded by moisture or a contaminant. In addition, the second electrode **140** may be peeled off from the first substrate **120**, and the moisture or the contaminant may penetrate into the emitting layer **138** through an interface between the peeled second electrode **140** and the first substrate **120**.

[0050] For the purpose of preventing the corrosion of the second electrode **140**, the second electrode **140** is formed inside the boundary of the second substrate **150**. For example, a first rectangular ring shape of the second electrode **140** exposed outside the passivation layer **142** may have a first width w_1 , a second rectangular ring shape between the boundary of the passivation layer **142** and the boundary of the second substrate **150** may have a second width w_2 , and a third rectangular ring shape of the seal pattern **144** may have a third width w_3 . The first width w_1 may be smaller than the second width w_2 ($w_1 < w_2$), and the third width w_3 may be equal to or smaller than a value of the first width w_1 subtracted from the second widths w_2 ($w_3 \leq (w_2 - w_1)$).

[0051] Accordingly, diffusion of remaining hydrogen of the passivation layer **142** is blocked by the second electrode **140** and reduction of the oxide semiconductor layer **126** of the driving TFT T is prevented, thereby a threshold voltage shift of the driving TFT T prevented.

[0052] For the purpose of preventing diffusion of hydrogen by the second electrode **140**, the second electrode **140** may include a material having a relatively low permeability of hydrogen. The second electrode **140** may include one of aluminum (Al), copper (Cu), silver (Ag), gold (Au) and platinum (Pt).

[0053] In addition, each of the second electrode **140** and the passivation layer **142** may be formed by using a shadow mask. For example, the second electrode **140** may be formed through an evaporation method or a physical vapor deposition (PVD) method. After a first shadow mask having a first open area is disposed over the emitting layer **138** on the first substrate **120**, a metallic material may be deposited through the first open area of the first shadow mask to form the second electrode **140** on the emitting layer **138**. Further, the passivation layer **142** may be formed through a chemical vapor deposition (CVD) method. After a second shadow mask having a second open area smaller than the first open area is disposed over the second electrode **140** on the first substrate **120**, an insulating material may be deposited through the second open area of the second shadow mask to form the passivation layer **142** on the second electrode **140**.

[0054] The second electrode **140** formed through an evaporation method may have a relatively weak adhesion to the first substrate **120**. For the purpose of obtaining reliability of adhesion between the first and second substrates **120** and **150**, the seal pattern **144** may be formed to contact the first and second substrates **120** and **150** directly and have a width equal to or greater than a reference value. For example, the seal pattern **144** may have the third width w_3 equal to or greater than about 0.05% of a diagonal length of the second substrate **150**.

[0055] Another embodiment where the first and second substrates are attached to each other with a sealant wholly formed between the first and second substrates instead of the seal pattern **144** will be illustrated with reference to drawings hereinafter.

[0056] FIG. 6 is a view showing an organic light emitting diode display device according to a second embodiment of the present invention, FIG. 7 is a cross-sectional view taken along a line VII-VII of FIG. 6.

[0057] In FIGS. 6 and 7, an organic light emitting diode (OLED) display device **210** includes first and second substrates **220** and **250**, an array layer **248**, a second electrode **240** and a passivation layer **242** sequentially on the first substrate **220** and a sealant **244** in an entire area between the first and second substrates **220** and **250**.

[0058] The first and second substrates **220** and **250** facing and spaced apart from each other include a plurality of pixel regions (not shown). Although not shown, the array layer **248** includes a gate line, a data line, a power line, a switching thin film transistor (TFT), a driving TFT, a first electrode and an emitting layer. The gate line, the data line and the power line cross each other to define the plurality of pixel regions. The switching TFT is coupled to the gate line and the data line, and the driving TFT is coupled to the switching TFT and the power line. The first electrode is coupled to the driving TFT, and the first electrode, the emitting layer and the second electrode **240** constitute a light emitting diode (LED).

[0059] Similarly to the first embodiment, the array layer **248** of the second embodiment is disposed in a display region at a central portion of the first and second substrates **220** and **250** and emits light for displaying an image. Although not shown, a gate electrode is formed in each pixel region on an inner surface of the first substrate **220** and a gate insulating layer is formed on the gate electrode. An oxide semiconductor layer is formed on the gate insulating layer corresponding to the gate electrode, and an etch stopper is formed on the oxide semiconductor layer.

[0060] Source and drain electrodes are formed on the etch stopper. The source and drain electrodes contact both end portions, respectively, of the oxide semiconductor layer. The gate electrode, the oxide semiconductor layer, the source electrode and the drain electrode constitute the driving TFT.

[0061] The oxide semiconductor layer may include an oxide semiconductor material such as indium gallium zinc oxide (IGZO), zinc indium oxide (ZIO), zinc gallium oxide (ZGO) and zinc tin oxide (ZTO). As a result, the driving TFT may have excellent electrical properties such as a relatively high mobility, a relatively low leakage current and a relatively constant static current.

[0062] A protecting layer is formed on the driving TFT. The protecting layer includes a drain contact hole exposing the drain electrode of the driving TFT.

[0063] The first electrode is formed on the protecting layer in each of the plurality of pixel regions, and a bank layer is formed on a boundary portion of the first electrode. The first

electrode is electrically coupled to the drain electrode of the driving TFT through the drain contact hole. The bank layer includes an opening exposing a central portion of the first electrode.

[0064] The emitting layer contacting the first electrode through the opening is formed on the bank layer, and the second electrode **240** is formed on the emitting layer. The first electrode, the emitting layer and the second electrode **240** constitute the LED. In addition, the passivation layer **242** is formed on the second electrode **240**.

[0065] The sealant **244**, which is referred to as a face seal, may be formed in an entire area between the first and second substrates **220** and **250**. The sealant **244** attaches the first and second substrates **220** and **250**, and a plurality of pads **246** coupled to a driving circuit (not shown) are formed on the first substrate **220** outside the sealant **244**. In addition, the sealant **244** may prevent permeation of an exterior moisture or an exterior contaminant and may absorb an exterior impact. The first substrate **220** is referred to as a lower substrate, a TFT substrate or a backplane, and the second substrate **250** is referred to as an encapsulation substrate.

[0066] In the OLED display device **210**, each of the second electrode **240** where a common voltage is applied and the passivation layer **242** protecting the LED from an exterior moisture or an exterior contaminant are formed as a single body covering the plurality of pixel regions. As a result, each of the second electrode **240** and the passivation layer **242** is formed on an entire surface of the first substrate **220**. In addition, the second electrode **240** is formed to have a larger area than the passivation layer **242** such that the passivation layer **242** is formed only on the second electrode **240**. Accordingly, the passivation layer **242** is formed inside a boundary of the second electrode **240**.

[0067] When each of the second electrode **240** and the passivation layer **242** is formed to have a rectangular shape, four sides of the second electrode **240** may be exposed outside the passivation layer **242**.

[0068] When the second electrode **240** is formed to exceed the sealant **244** and have a larger area than the second substrate **250**, the second electrode **240** may be corroded by a moisture or a contaminant. In addition, the second electrode **240** may be peeled off from the first substrate **220**, and the moisture or the contaminant may penetrate into the emitting layer through an interface between the peeled second electrode **240** and the first substrate **220**.

[0069] For the purpose of preventing corrosion of the second electrode **240**, the second electrode **240** is formed inside the boundary of the second substrate **250**. For example, a first rectangular ring shape of the second electrode **240** exposed outside the passivation layer **242** may have a first width w_1 and a second rectangular ring shape between the boundary of the passivation layer **242** and the boundary of the second substrate **150** may have a second width w_2 . The first width w_1 may be smaller than the second width w_2 ($w_1 < w_2$).

[0070] Accordingly, diffusion of remaining hydrogen of the passivation layer **242** is blocked by the second electrode **240**, preventing reduction of the oxide semiconductor layer of the driving TFT, and further preventing a threshold voltage shift of the driving TFT.

[0071] For the purpose of preventing diffusion of hydrogen by the second electrode **240**, the second electrode **240** may include a material having a relatively low permeability of

hydrogen. For example, the second electrode **240** may include one of aluminum (Al), copper (Cu), silver (Ag), gold (Au) and platinum (Pt).

[0072] In addition, each of the second electrode **240** and the passivation layer **242** may be formed by using a shadow mask. For example, the second electrode **240** may be formed through an evaporation method or a physical vapor deposition (PVD) method. After a first shadow mask having a first open area is disposed over the emitting layer on the first substrate **220**, a metallic material may be deposited through the first open area of the first shadow mask to form the second electrode **240** on the emitting layer. Further, the passivation layer **242** may be formed through a chemical vapor deposition (CVD) method. After a second shadow mask having a second open area smaller than the first open area is disposed over the second electrode **240** on the first substrate **220**, an insulating material may be deposited through the second open area of the second shadow mask to form the passivation layer **242** on the second electrode **240**.

[0073] Consequently, in an exemplary embodiment of the OLED display device, the passivation layer is formed to have a smaller area than the second electrode, therefore the diffusion of hydrogen remaining in the passivation layer is blocked by the second electrode. As a result, the reduction of the semiconductor material of the TFTs and the threshold voltage shift of the TFTs are prevented. In addition, deterioration such as stain or brightness deviation in an image is prevented and display quality of the OLED display device is improved.

[0074] It will be apparent to those skilled in the art that various modifications and variations can be made in embodiments of the present invention without departing from the spirit or scope of the invention. Thus, it is intended that the present invention cover the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

[0075] A number of examples have been described above. Nevertheless, it will be understood that various modifications may be made. For example, suitable results may be achieved if the described techniques are performed in a different order and/or if components in a described system, architecture, device, or circuit are combined in a different manner and/or replaced or supplemented by other components or their equivalents. Accordingly, other implementations are within the scope of the following claims.

What is claimed is:

1. A method of fabricating an organic light emitting diode display device, comprising:

forming a gate line and a data line on a first substrate, the gate line and the data line crossing each other to define a plurality of pixel regions;

forming at least one thin film transistor coupled to the gate line and the data line;

forming a light emitting diode coupled to the at least one thin film transistor, the light emitting diode including a first electrode, an emitting layer and a second electrode;

forming a passivation layer on the light emitting diode, the passivation layer having a smaller area than the second electrode; and

attaching a second substrate to the first substrate having the passivation layer.

2. The method of claim 1, wherein each of the second electrode and the passivation layer is formed as a single body covering the plurality of pixel regions.

3. The method of claim 2, wherein the passivation layer is formed on the second electrode, and the second electrode is exposed outside the passivation layer.

4. The method of claim 1, wherein the second electrode is formed through an evaporation method using a first shadow mask having a first open area.

5. The method of claim 4, wherein the passivation layer is formed through a chemical vapor deposition method using a second shadow mask having a second open area smaller than the first open area.

6. The method of claim 3, wherein a first rectangular ring shape of the second electrode exposed outside the passivation layer has a first width, and a second rectangular ring shape between a boundary of the passivation layer and a boundary of the second substrate has a second width greater than the first width.

7. The method of claim 6, further comprising forming a seal pattern in an edge portion between the first and second substrates, wherein the first and second substrates are attached to each other by the seal pattern.

8. The method of claim 7, wherein a third rectangular ring shape of the seal pattern has a third width not greater than a value of the first width subtracted from the second width.

9. The method of claim 8, wherein the third width is not smaller than about 0.05% of a diagonal length of the second substrate.

10. The method of claim 6, further comprising forming a sealant in an entire area between the first and second substrates, wherein the first and second substrates are attached to each other by the sealant.

11. The method of claim 1, wherein the second electrode includes one of aluminum (Al), copper (Cu), silver (Ag), gold (Au) and platinum (Pt).

12. The method of claim 1, wherein the at least one thin film transistor includes an oxide semiconductor layer including one of indium gallium zinc oxide (IGZO), zinc indium oxide (ZIO), zinc gallium oxide (ZGO) and zinc tin oxide (ZTO).

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专利名称(译)	有机发光二极管显示装置及其制造方法		
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摘要(译)

一种有机发光二极管显示装置，包括：第一基板和第二基板，彼此面对并且彼此间隔开；栅极线和数据线在第一基板上，栅极线和数据线彼此交叉以限定多个像素区域；至少一个薄膜晶体管耦合到栅极线和数据线；发光二极管，耦合到所述至少一个薄膜晶体管，所述发光二极管包括第一电极，发光层和第二电极；在发光二极管上形成钝化层，钝化层的面积小于第二电极的面积。

